FAIRCHILD SEMICONDUCTOR TM

TN6716A

C B E

TO-226

NPN General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 1.2A. Sourced from Process 38. See TN6715A for characteristics.

Absolute Maximum Ratings*

T_A = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	60	V
V_{CBO}	Collector-Base Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current - Continuous	2	A
$T_{J,\ Tstg}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150°C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

T_A = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		T_A=25°C	
P_D	Total Device Dissipation Derate above 25°C	1 8	W mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	°C/W

NPN General Purpose Amplifier

(continued)

Electrical Characteristics

$T_{A = 25°C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C = 1 mA	60		V
BV_{CBO}	Collector-Base Breakdown Voltage	I_C = 100 µA	60		V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E = 1 mA	5		V
I_{CBO}	Collector Cutoff Current	V_{CB} = 40 V		100	nA
I_{EBO}	Emitter Cutoff Current	V_{EB} = 5 V		10	uA
ON CHARACTERISTICS					
h_{FE}	DC Current Gain	I_C = 50 mA, V_{CE} = 1 V I_C = 250 mA, V_{CE} = 1 V I_C = 500 mA, V_{CE} = 1 V	80 50 20	250	-
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 250 mA, I_B = 10 mA I_C = 250 mA, I_B = 25 mA		0.5 0.35	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C = 250 mA, V_{CE} = 1.0 V		1.2	V
SMALL SIGNAL CHARACTERISTICS					
C_{cb}	Output Capacitance	V_{CB} = 10 V, I_E = 0, f = 1MHz		30	pF
hfe	Small Signal Current Gain	I_C = 200 mA,V_{CE} = 5 V,f=20MHz	2.5	25	MHz

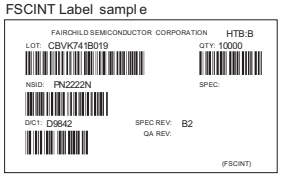
*Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 1.0%

TO-226AE Tape and Reel Data and Package Dimensions

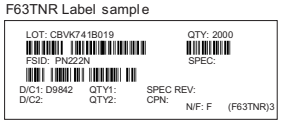
FAIRCHILD SEMICONDUCTOR™

TO-226AE Packaging
Configuration: Figure 1.0

FSCINT Label sample

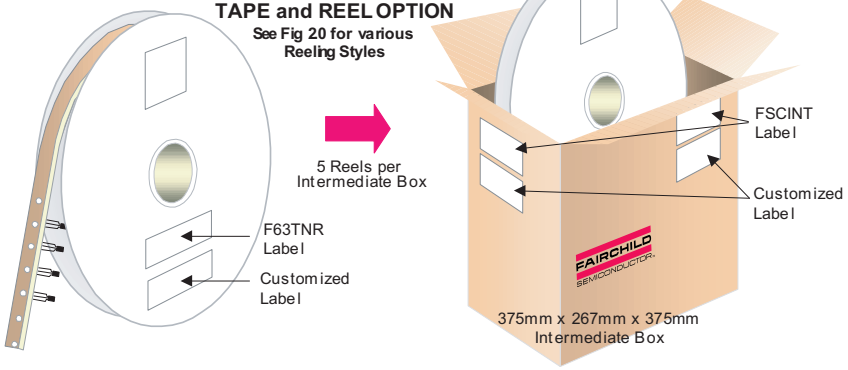


F63TNR Label sample



TAPE and REEL OPTION

See Fig 20 for various Reeling Styles



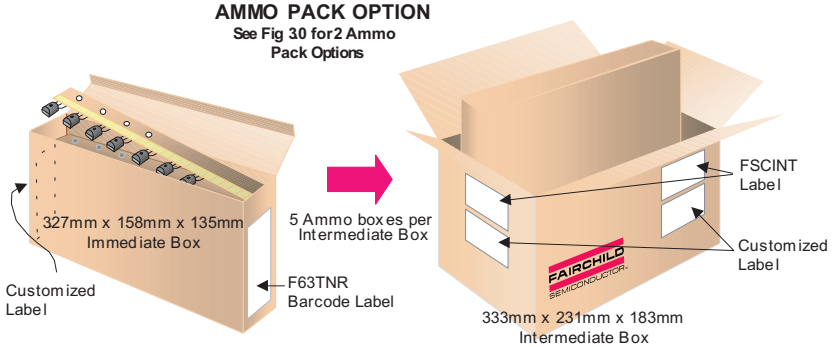
AMMO PACK OPTION

See Fig 30 for2 Ammo Pack Options

TO-226AE TNR/AMMO PACKING INFORMATION

Packing	Style	Quantity	EOL code
Reel	A	2,000	D26Z
	E	2,000	D27Z
Ammo	M	2,000	D74Z
	P	2,000	D75Z

Unit weight = 0.300gm
Reel weight with components = 0.868 kg
Ammo weight with components = 0.880 kg
Max quantity per intermediate box = 10,000 units

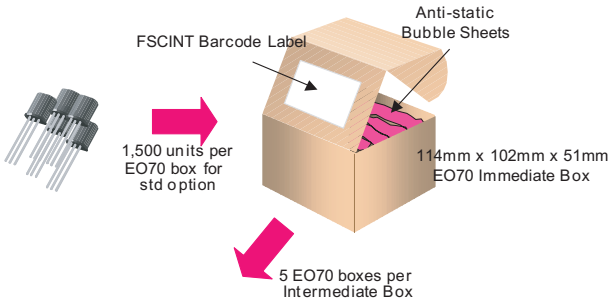


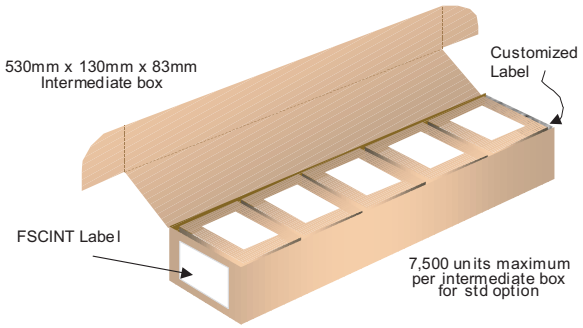
BULK OPTION

See Bulk Packing Information table

(TO-226AE) BULK PACKING INFORMATION

EOL CODE	DESCRIPTION	LEADCLIP DIMENSION	QUANTITY
J18Z	TO-18 OPTION STD	NO LEAD CLIP	1.0 K / BOX
J05Z	TO-5 OPTION STD	NO LEAD CLIP	1.0 K / BOX
NO EOL CODE	TO-226 STANDARD STRAIGHT	NO LEADCLIP	1.5 K / BOX

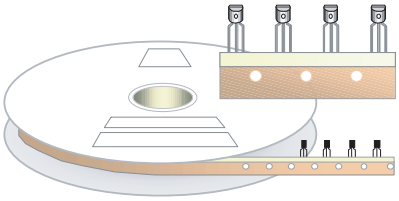




TO-226AE Tape and Reel Data and Package Dimensions, continued

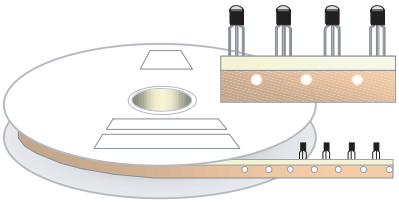
TO-226AE Reeling Style
Configuration: Figure 2.0

Machine Option "A" (H)



Style "A", D26Z, D70Z (s/h)

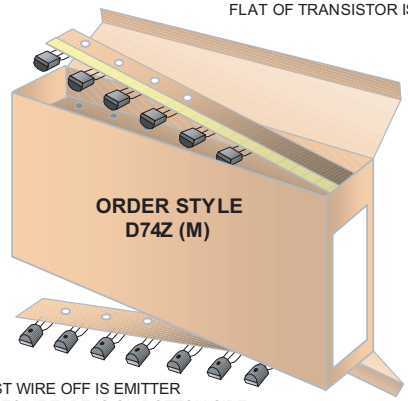
Machine Option "E" (J)



Style "E", D27Z, D71Z (s/h)

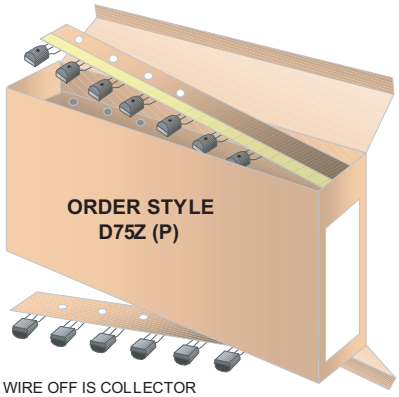
TO-226AE Radial Ammo Packaging
Configuration: Figure 3.0

FIRST WIRE OFF IS COLLECTOR (ON PKG. 92)
ADHESIVE TAPE IS ON THE TOP SIDE
FLAT OF TRANSISTOR IS ON TOP



FIRST WIRE OFF IS EMITTER
ADHESIVE TAPE IS ON BOTTOM SIDE
FLAT OF TRANSISTOR IS ON BOTTOM

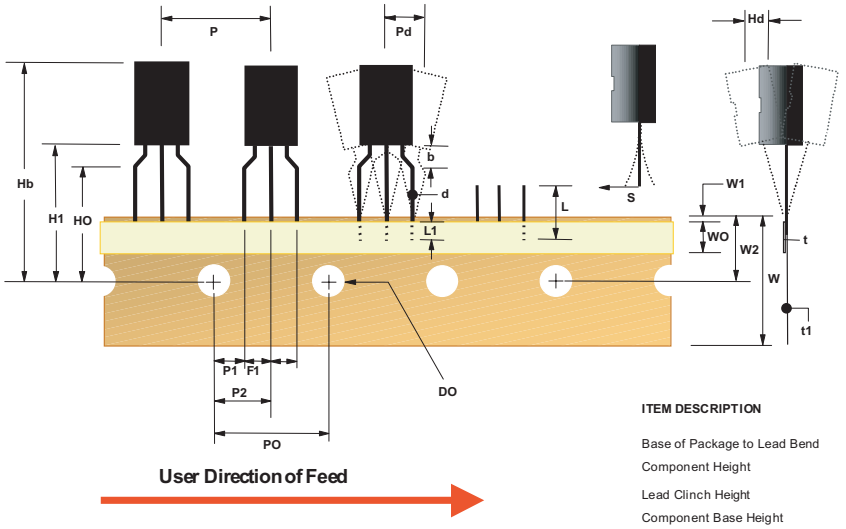
FIRST WIRE OFF IS EMITTER (ON PKG. 92)
ADHESIVE TAPE IS ON THE TOP SIDE
FLAT OF TRANSISTOR IS ON BOTTOM



FIRST WIRE OFF IS COLLECTOR
ADHESIVE TAPE IS ON BOTTOM SIDE
FLAT OF TRANSISTOR IS ON TOP

TO-226AE Tape and Reel Data and Package Dimensions, continued

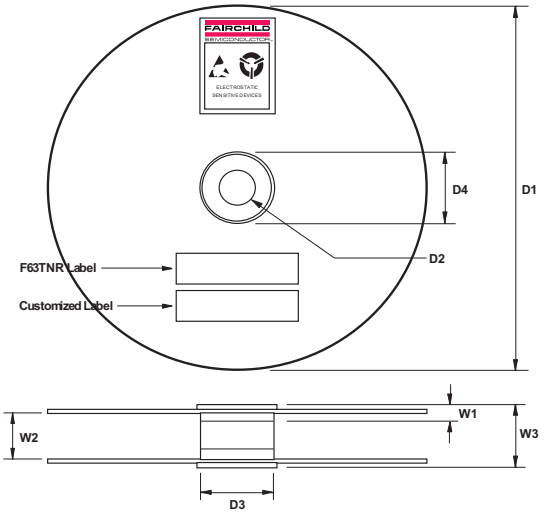
TO-226AE Tape and Reel Taping Dimension Configuration: Figure 4.0



ITEM DESCRIPTION	SYMBOL	DIMENSION
Base of Package to Lead Bend	b	0.098 (max)
Component Height	Hb	1.078 (+/- 0.050)
Lead Clinch Height	HO	0.630 (+/- 0.020)
Component Base Height	H1	0.748 (+/- 0.020)
Component Alignment (side/side)	Pd	0.040 (max)
Component Alignment (front/back)	Hd	0.031 (max)
Component Pitch	P	0.500 (+/- 0.020)
Feed Hole Pitch	PO	0.500 (+/- 0.008)
Hole Center to First Lead	P1	0.150 (+0.009, -0.010)
Hole Center to Component Center	P2	0.247 (+/- 0.007)
Lead Spread	F1/F2	0.104 (+/- 0 .010)
Lead Thickness	d	0.018 (+0.002, -0.003)
Cut Lead Length	L	0.429 (max)
Taped Lead Length	L1	0.209 (+0.051, -0.052)
Taped Lead Thickness	t	0.032 (+/- 0.006)
Carrier Tape Thickness	t1	0.021 (+/- 0.006)
Carrier Tape Width	W	0.708 (+0.020, -0.019)
Hold - down Tape Width	WO	0.236 (+/- 0.012)
Hold - down Tape position	W1	0.035 (max)
Feed Hole Position	W2	0.360 (+/- 0.025)
Sprocket Hole Diameter	DO	0.157 (+0.008, -0.007)
Lead Spring Out	S	0.004 (max)

Note : All dimensions are in inches.

TO-226AE Reel Configuration: Figure 5.0

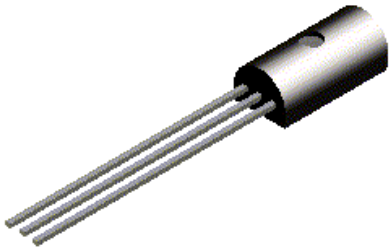


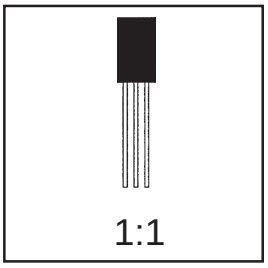
ITEM DESCRIPTION	SYMBOL	MINIMUM	MAXIMUM
Reel Diameter	D1	13.975	14.025
Arbor Hole Diameter (Standard)	D2	1.160	1.200
(Small Hole)	D2	0.650	0.700
Core Diameter	D3	3.100	3.300
Hub Recess Inner Diameter	D4	2.700	3.100
Hub Recess Depth	W1	0.370	0.570
Flange to Flange Inner Width	W2	1.630	1.690
Hub to Hub Center Width	W3		2.090

Note: All dimensions are inches

TO-226AE Tape and Reel Data and Package Dimensions, continued

TO-226AE (FS PKG Code 95, 99)

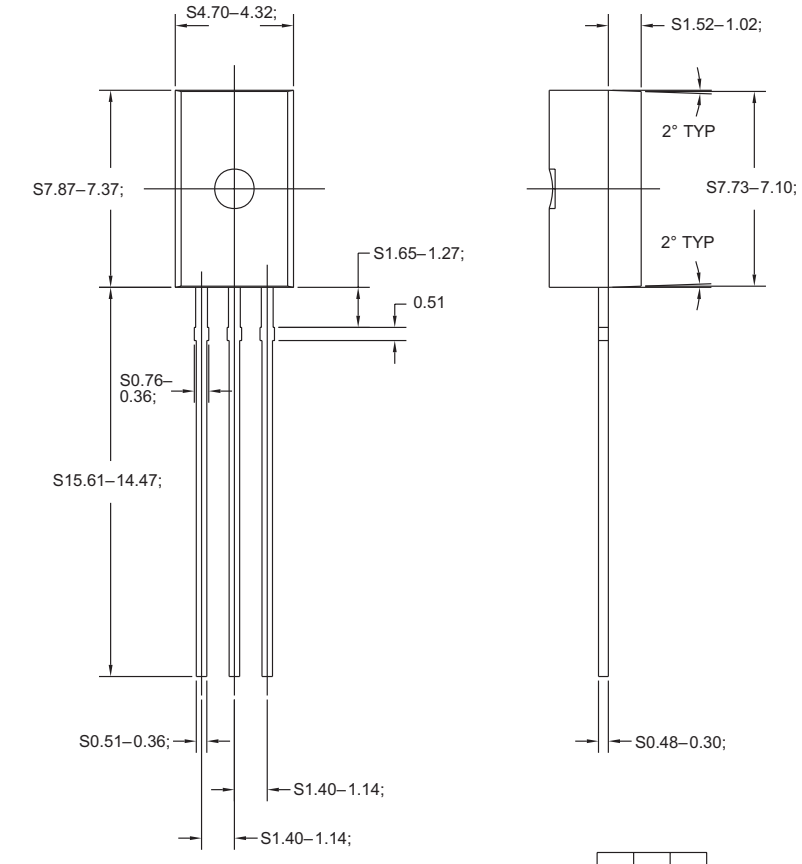




Scale 1:1 on letter size paper

Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.300



PIN	99	95
1	E	E
2	B	C
3	C	B

TO-226AE (95,99)

For leadformed option ordering,
refer to Tape & Reel data information.

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